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RFMD(R) Introduces GaN High-Power Transistor Product Family; Company Currently Sampling Lead Base Station Customers

SAN FRANCISCO, Jun 13, 2006 (BUSINESS WIRE) -- RFMD® (Nasdaq: RFMD), a global leader in the design and manufacture of high-performance radio systems and solutions for applications that drive mobile communications, today introduced a family of Gallium Nitride (GaN) High Electron Mobility Transistor (HEMT) high-power transistors and is sampling to top-tier cellular infrastructure and WiMAX base station customers. The sampling of these transistors represents the achievement of a baseline 0.5um GaN high-power transistor process by RFMD.

"The infrastructure market is a key growth area for RFMD that leverages our existing technological and manufacturing expertise," said Jeff Shealy, Vice President, Infrastructure Product Group for RFMD. "With the achievement of our baseline GaN process technology, we are positioned to provide customers with the high-power, broadband solutions that are needed to meet their growing demand for more cost-effective and more efficient deployment of next-generation wireless infrastructure."

"For cellular infrastructure and WiMAX base station OEMs dependant on maximizing power and efficiency, RFMD's GaN transistors provide higher at-package matching impedence, higher power density and wider bandwidth performance when compared with silicon LDMOS devices," said Bill Pratt, Co-founder, Chief Technical Officer and Corporate Vice President for RFMD. "In addition, RFMD is the world's largest manufacturer of GaAs wafers and is able to achieve distinct cost advantages by utilizing our high-volume manufacturing environment at our Greensboro, North Carolina, headquarters."

These high power devices show excellent peak drain efficiency up to 67% at UMTS and up to 60% at WiMAX frequency bands. RFMD has achieved high gain of 16dB, high power density of up to 4W/mm at 28V and 1,000 hour high temperature reliability results.

RFMD's GaN HEMT transistors for the wireless cellular market are targeted to the UMTS or 3G base station segment and include the RF3820 (8W), RF3912 (60W), RF3913 (90W) and RF3914 (120W). RFMD's GaN HEMT transistors targeted to the emerging WiMAX base station segment include the 2.5 GHz RF3916 (50W), RF3917 (75W), RF3918 (100W) and 3.5 GHz RF3821 (8W), RF3919 (50W).

For more information about this and other RFMD products and services, be sure to visit RFMD at IEEE MTT-S International Microwave Symposium 2006 in San Francisco, California, June 13-15, 2006 at booth 1207.

About RFMD

RFMD is a global leader in the design and manufacture of high-performance radio systems and solutions for applications that drive mobile communications. RFMD's power amplifiers, transmit modules, cellular transceivers and system-on-chip (SOC) solutions enable worldwide mobility, provide enhanced connectivity and support advanced functionality in current- and next-generation mobile handsets, cellular base stations, wireless local area networks (WLANs), wireless personal area networks (WPANs) and global positioning systems (GPS). Recognized for its diverse portfolio of state-of-the-art semiconductor technologies and vast RF systems expertise, RFMD is a preferred supplier enabling the world's leading mobile device manufacturers to deliver advanced wireless capabilities that satisfy current and future market demands.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001- and ISO 14001-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ National Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in quarterly operating results, the rate of growth and development of wireless markets, risks

associated with the operation of our wafer fabrication facilities, molecular beam epitaxy facility, our assembly facility and our test, tape and reel facilities, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, our ability to reduce costs and improve gross margins by implementing innovative technologies, our ability to bring new products to market, dependence on consignment sales through customer inventory hubs, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on a limited number of customers, dependence on third parties and the variability of future stock-based compensation charges or credits during the remainder of fiscal 2006 as a result of our stock option exchange program as well as the adoption of SFAS 123R in fiscal 2007. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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SOURCE: RFMD®

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